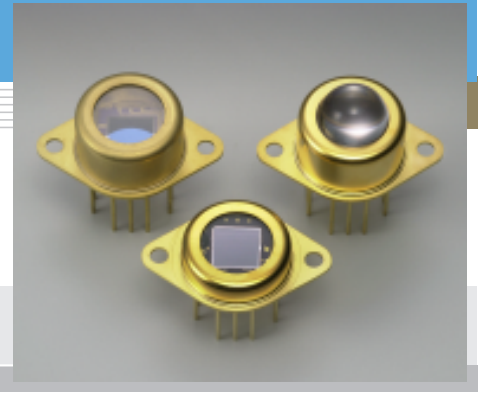


Si photodiode with preamp S6204 series

Large area photodiode integrated with op amp and TE-cooler



S6204 series is a thermoelectrically cooled Si photodiode developed for low-light-level detection. A large area photodiode, op amp, TE-cooler and feedback resistor (10 GΩ) are integrated into a single package. A thermistor is also included in the same package for temperature control so that the photodiode and I-V conversion circuit can be cooled for stable operation. S6204 series also features low noise and low NEP, and is especially suitable for NOx detection.

Features

- Large active area size
S6204/-01: 10 × 10 mm
S6204-03 : φ15.6 mm (lens)
- UV to NIR Si photodiode optimized for precision photometry
- Compact hermetic package with sapphire window
- High precision FET input operational amplifier
- High gain: Rf=10 GΩ
- Low noise and NEP
- High cooling efficiency
S6204/-03: ΔT=50 °C
S6204-01 : ΔT=30 °C
- High stability with thermistor

Applications

- NOx detection
- Low-light-level measurement

S6204 series may be damaged by Electro Static Discharge, etc. Please see Precautions for use in the last page.

Absolute maximum ratings

Parameter	Symbol	Value
Supply voltage (preamp)	Vcc	±18 V
Reverse voltage (S6204-03, photodiode)	VR	30 V
Operating temperature	Topr	-30 to +60 °C
Storage temperature	Tstg	-40 to +80 °C
Operating temperature (photodiode)	Tdopr	-30 to +60 °C
TE-cooler allowable voltage *1	Vte	5 V
TE-cooler allowable current	Ite	1 A
Thermistor power dissipation	Pth	0.2 mW

*1: Max ripple: 10 %

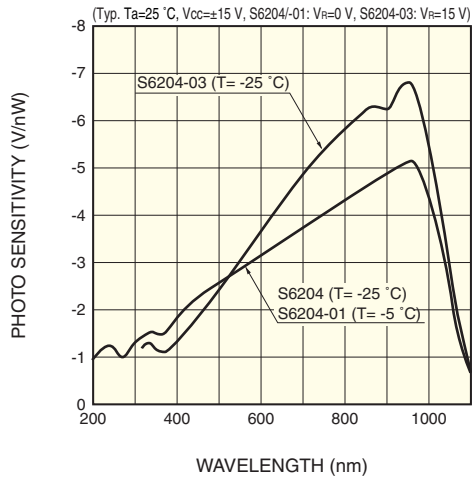
Recommended operating conditions

Parameter	Symbol	S6204/-01	S6204-03
Supply voltage (preamp)	Vcc	±5 to ±15 V	
Reverse voltage (photodiode)	VR	0 V	15 V
TE-cooler current	Ite	0.8 A Max.	
Thermistor power dissipation	Pth	0.03 mW Max.	
Load resistance	RL	100 kΩ Min.	

Electrical and optical characteristics (Typ. Ta=25 °C, Vcc=±15 V, RL=1 MΩ)

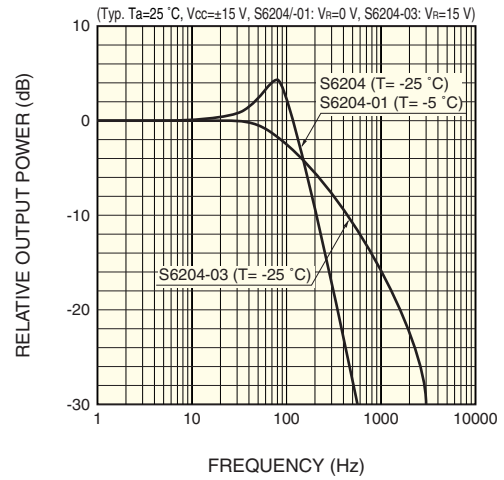
Parameter	Symbol	Condition	S6204	S6204-01	S6204-03	Unit
			T= -25 °C VR=0 V	T= -5 °C VR=0 V	T= -25 °C VR=15 V	
Spectral response range	λ		190 to 1100		320 to 1100	nm
Peak sensitivity wavelength	λp		960			nm
Feedback resistance	Rf		10			GΩ
Photo sensitivity	S	λ=200 nm	-0.9	-0.9		V/nW
		λ=λp	-5.1	-5.1	-6.5	
Output noise voltage	Vn	Dark state, f=10 Hz	42	50	13	μVrms/Hz ^{1/2}
Noise equivalent power	NEP	λ=λp, f=10 Hz	9	10	2	fW/Hz ^{1/2}
Output offset voltage	Vos	Dark state	±2	±2	±3	mV
Cut-off frequency	fc	-3 dB	130			Hz
Output voltage swing	Vo		-13			V
Supply current	Icc	Dark state	0.6			mA
Thermistor resistance	Rth		86	30	86	kΩ

Spectral response



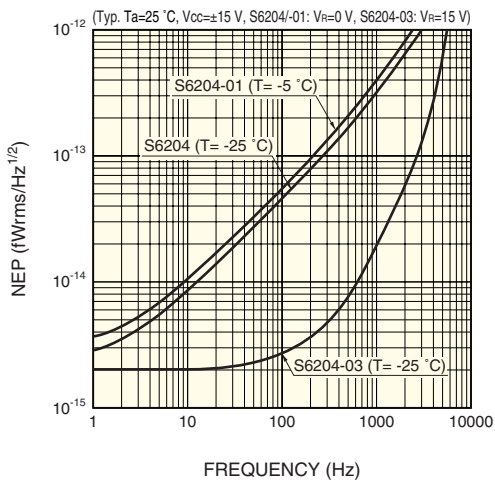
KSPDB0147EA

Frequency response



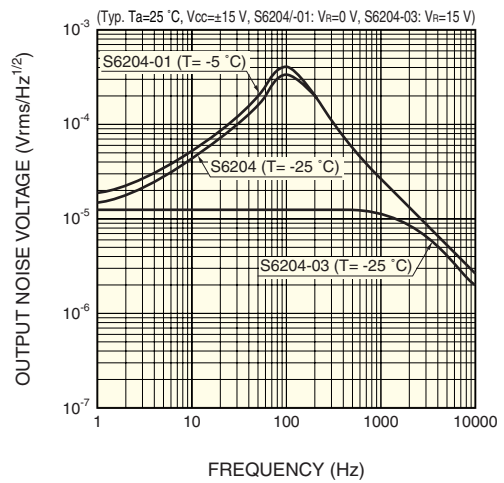
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NEP vs. frequency



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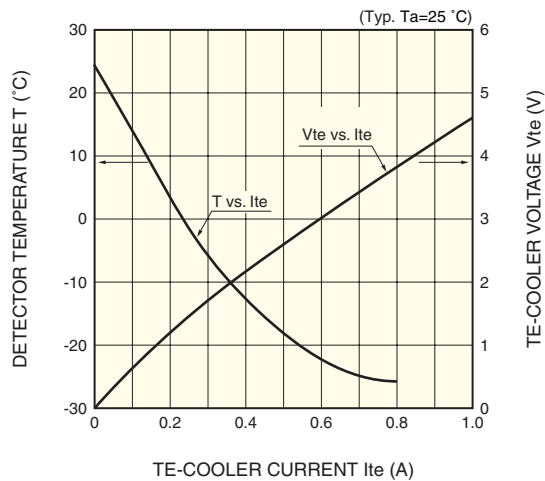
Output noise voltage vs. frequency



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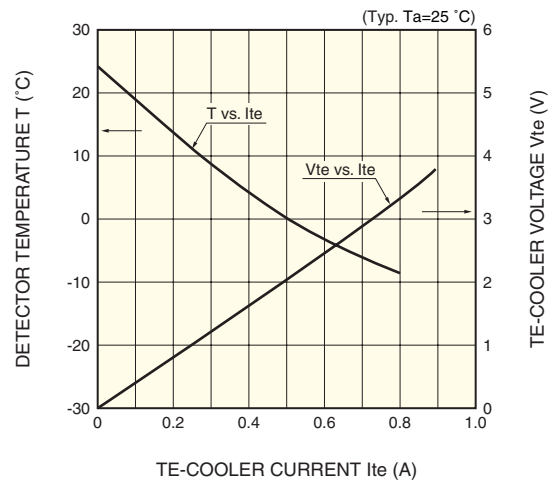
Detector temperature vs. TE-cooler current

S6204/-03



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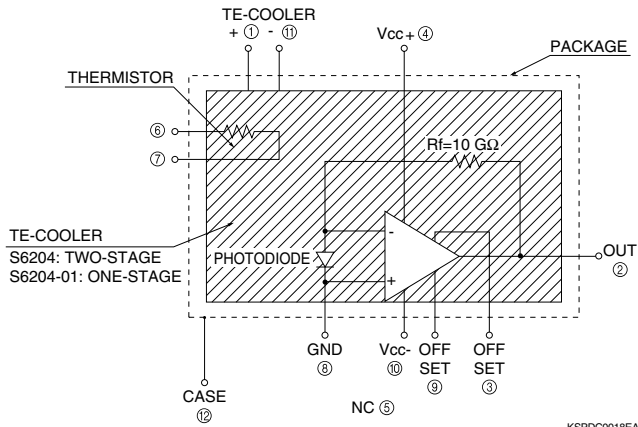
S6204-01



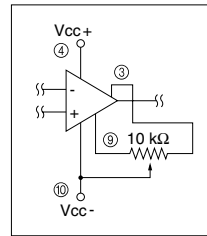
KSPDB0172EA

External connection

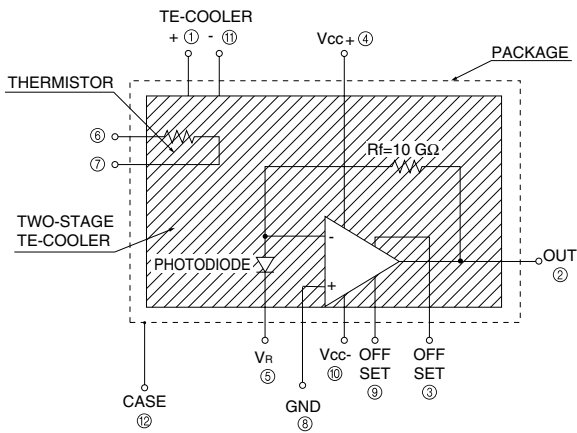
S6204/-01



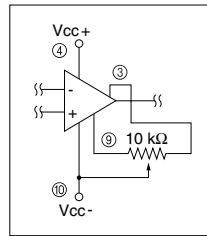
OFFSET VOLTAGE NULLING



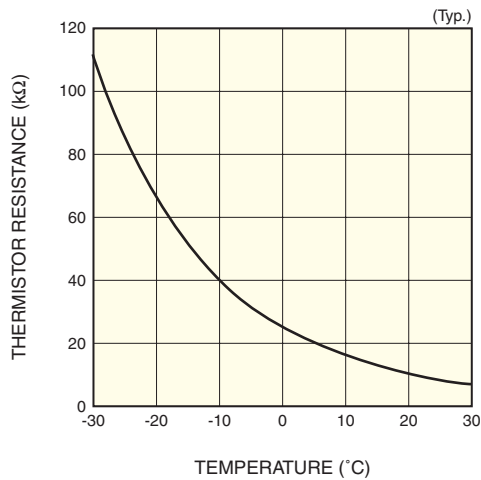
S6204-03



OFFSET VOLTAGE NULLING



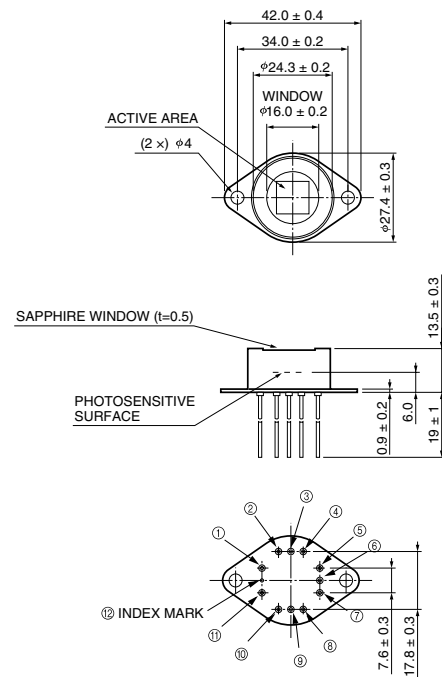
Thermistor resistance vs. temperature



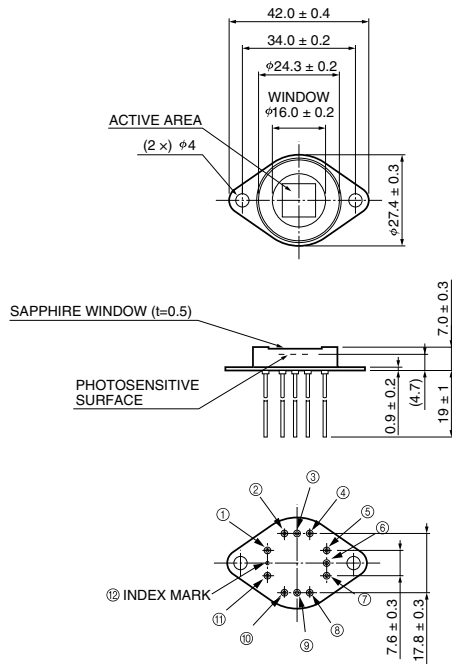
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Dimensional outlines (unit: mm)

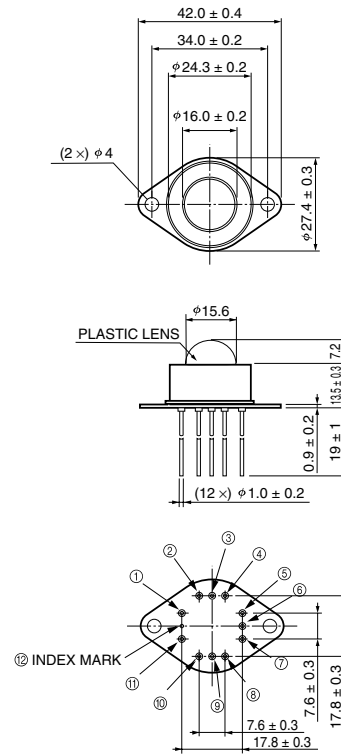
S6204



KSPDA0071EB

S6204-01

KSPDA0079EA

S6204-03

KSPDA0088EB

A tantalum or ceramic capacitor of 0.1 to 10 μF must be connected to the supply voltage leads (pins ④ and ⑩) as a bypass capacitor used to prevent the device from oscillation.

Precautions for use

■ ESD

S6204 series may be damaged or their performance may deteriorate by such factors as electro static discharge from the human body, surge voltage from measurement equipment, leakage voltages from soldering irons and packing materials. As a countermeasure against electro static discharge, the device, operator, work place and measuring jigs must all be set at the same potential. The following precautions must be observed during use:

- To protect the device from electro static discharge which accumulate on the operator or the operator's clothes, use a wrist strap or similar tools to ground the operator's body via a high impedance resistor (1 M Ω).
- A semiconductive sheet (1 M Ω to 10 M Ω) should be laid on both the work table and the floor in the work area.
- When soldering, use an electrically grounded soldering iron with an isolation resistance of more than 10 M Ω .
- For containers and packing, use of a conductive material or aluminum foil is effective. When using an antistatic material, use one with a resistance of 0.1 M Ω/cm^2 to 1 G Ω/cm^2 .

■ Strength

Thermoelectrically-cooled devices may be damaged if subjected to shock, for example drop impact. Take sufficient care when handling these devices.

■ Lead forming

When forming the leads, take care not to apply excessive force to the lead sealing glass. Excessive force may impair the hermetic sealing, possibly degrading the cooling capacity.

To form the leads, hold the roots of the leads securely with a pair of pliers and bend them.

■ Heatsink

Use a heatsink with thermal resistance less than 1.3 $^{\circ}\text{C}/\text{W}$. Apply thermal grease between the heatsink and detector package, and then fasten them with the screws. Be careful not to give any excessive force or mechanical stress to the detector package at this point.

■ Wiring

Be careful not to misconnect the plus and minus leads of the thermoelectric cooler or preamplifier. Supplying a voltage or current while these connections are reversed may damage the device.

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